

# MOSFET

Metal Oxide Semiconductor Field Effect Transistor

## CoolMOS™ C6 600V

600V CoolMOS™ C6 Power Transistor  
IPx60R950C6

## Data Sheet

Rev. 2.5  
Final

## 600V CoolMOS™ C6 Power Transistor

IPD60R950C6, IPB60R950C6  
IPP60R950C6, IPA60R950C6

### 1 Description

CoolMOS™ is a revolutionary technology for high voltage power MOSFETs, designed according to the superjunction (SJ) principle and pioneered by Infineon Technologies. CoolMOS™ C6 series combines the experience of the leading SJ MOSFET supplier with high class innovation. The resulting devices provide all benefits of a fast switching SJ MOSFET while not sacrificing ease of use. Extremely low switching and conduction losses make switching applications even more efficient, more compact, lighter, and cooler.

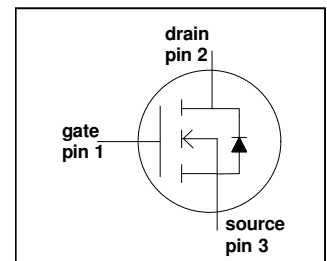
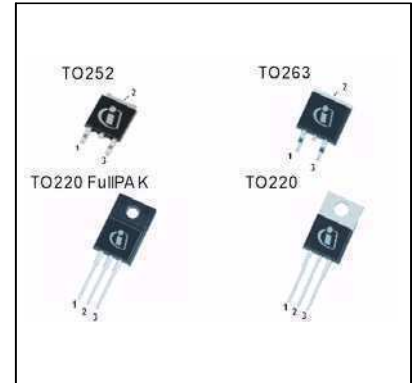
#### Features

- Extremely low losses due to very low FOM  $R_{DS(on)} \cdot Q_g$  and  $E_{oss}$
- Very high commutation ruggedness
- Easy to use/drive
- Fully qualified according to JEDEC for Industrial Applications
- Pb-free plating, Halogen free mold compound

#### Applications

PFC stages, hard switching PWM stages and resonant switching PWM stages for e.g. PC Silverbox, Adapter, LCD & PDP TV, Lighting, Server, Telecom and UPS.

*Please note: For MOSFET paralleling the use of ferrite beads on the gate or separate totem poles is generally recommended.*



**Table 1 Key Performance Parameters**

Parameter	Value	Unit
$V_{DS} @ T_{j,max}$	650	V
$R_{DS(on),max}$	0.95	$\Omega$
$Q_{g,typ}$	13	nC
$I_{D,pulse}$	12	A
$E_{oss} @ 400V$	1.3	$\mu J$
Body diode $di/dt$	500	A/ $\mu s$

Type / Ordering Code	Package	Marking	Related Links
IPD60R950C6	PG-TO252	6R950C6	<a href="#">IFX C6 Product Brief</a> <a href="#">IFX C6 Portfolio</a> <a href="#">IFX CoolMOS Webpage</a> <a href="#">IFX Design tools</a>
IPB60R950C6	PG-TO263		
IPP60R950C6	PG-TO220		
IPA60R950C6	PG-TO220 FullPAK		

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## 2 Maximum Ratings

at  $T_j = 25\text{ °C}$ , unless otherwise specified.

**Table 2 Maximum ratings**

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Continuous drain current <sup>1)</sup>	$I_D$	-	-	4.4	A	$T_C = 25\text{ °C}$
				2.8		$T_C = 100\text{ °C}$
Pulsed drain current <sup>2)</sup>	$I_{D,pulse}$	-	-	12	A	$T_C = 25\text{ °C}$
Avalanche energy, single pulse	$E_{AS}$	-	-	46	mJ	$I_D = 0.8\text{ A}, V_{DD} = 50\text{ V}$ (see table 21)
Avalanche energy, repetitive	$E_{AR}$	-	-	0.13		$I_D = 0.8\text{ A}, V_{DD} = 50\text{ V}$
Avalanche current, repetitive	$I_{AR}$	-	-	0.8	A	
MOSFET dv/dt ruggedness	dv/dt	-	-	50	V/ns	$V_{DS} = 0 \dots 480\text{ V}$
Gate source voltage	$V_{GS}$	-20	-	20	V	static
		-30		30		AC ( $f > 1\text{ Hz}$ )
Power dissipation for TO-220, TO-252, TO-263	$P_{tot}$	-	-	37	W	$T_C = 25\text{ °C}$
Power dissipation for TO-220 FullPAK	$P_{tot}$	-	-	26	W	$T_C = 25\text{ °C}$
Operating and storage temperature	$T_j, T_{stg}$	-55	-	150	°C	
Mounting torque TO-220		-	-	60	Ncm	M3 and M3.5 screws
				50		M2.5 screws
TO-220FP						
Continuous diode forward current	$I_S$	-	-	3.9	A	$T_C = 25\text{ °C}$
Diode pulse current <sup>2)</sup>	$I_{S,pulse}$	-	-	12	A	$T_C = 25\text{ °C}$
Reverse diode dv/dt <sup>3)</sup>	dv/dt	-	-	15	V/ns	$V_{DS} = 0 \dots 480\text{ V}, I_{SD} \leq I_D,$ $T_j = 125\text{ °C}$
Maximum diode commutation speed <sup>3)</sup>	di <sub>r</sub> /dt			500	A/μs	(see table 22)

1) Limited by  $T_{j,max}$ . Maximum duty cycle  $D = 0.75$

2) Pulse width  $t_p$  limited by  $T_{j,max}$

3) Identical low side and high side switch with identical  $R_G$

### 3 Thermal characteristics

**Table 3 Thermal characteristics TO-220 (IPP60R950C6)**

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Thermal resistance, junction - case	$R_{thJC}$	-	-	3.41	°C/W	leaded
Thermal resistance, junction - ambient	$R_{thJA}$	-	-	62		
Soldering temperature, wavesoldering only allowed at leads	$T_{sold}$	-	-	260	°C	1.6 mm (0.063 in.) from case for 10 s

**Table 4 Thermal characteristics TO-220FullIPAK (IPA60R950C6)**

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Thermal resistance, junction - case	$R_{thJC}$	-	-	4.9	°C/W	leaded
Thermal resistance, junction - ambient	$R_{thJA}$	-	-	80		
Soldering temperature, wavesoldering only allowed at leads	$T_{sold}$	-	-	260	°C	1.6 mm (0.063 in.) from case for 10 s

**Table 5 Thermal characteristics TO-263 (IPB60R950C6), TO-252 (IPD60R950C6)**

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Thermal resistance, junction - case	$R_{thJC}$	-	-	3.41	°C/W	SMD version, device on PCB, minimal footprint
Thermal resistance, junction - ambient	$R_{thJA}$	-	-	62		
			35			
Soldering temperature, wave- & reflowsoldering allowed	$T_{sold}$	-	-	260	°C	reflow MSL1

1) Device on 40mm\*40mm\*1.5 epoxy PCB FR4 with 6cm<sup>2</sup> (one layer, 70µm thick) copper area for drain connection. PCB is vertical without air stream cooling

## 4 Electrical characteristics

Electrical characteristics, at  $T_J=25\text{ °C}$ , unless otherwise specified

**Table 6 Static characteristics**

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Drain-source breakdown voltage	$V_{(BR)DSS}$	600	-	-	V	$V_{GS}=0\text{ V}$ , $I_D=0.25\text{ mA}$
Gate threshold voltage	$V_{GS(th)}$	2.5	3	3.5		$V_{DS}=V_{GS}$ , $I_D=0.13\text{ mA}$
Zero gate voltage drain current	$I_{DSS}$	-	-	1	$\mu\text{A}$	$V_{DS}=600\text{ V}$ , $V_{GS}=0\text{ V}$ , $T_J=25\text{ °C}$
		-	10	-		$V_{DS}=600\text{ V}$ , $V_{GS}=0\text{ V}$ , $T_J=150\text{ °C}$
Gate-source leakage current	$I_{GSS}$	-	-	100	nA	$V_{GS}=20\text{ V}$ , $V_{DS}=0\text{ V}$
Drain-source on-state resistance	$R_{DS(on)}$	-	0.86	0.95	$\Omega$	$V_{GS}=10\text{ V}$ , $I_D=1.5\text{ A}$ , $T_J=25\text{ °C}$
		-	2.22	-		$V_{GS}=10\text{ V}$ , $I_D=1.5\text{ A}$ , $T_J=150\text{ °C}$
Gate resistance	$R_G$	-	16	-	$\Omega$	$f=1\text{ MHz}$ , open drain

**Table 7 Dynamic characteristics**

Parameter	Symbol	Values			Unit	Note / Test Condition	
		Min.	Typ.	Max.			
Input capacitance	$C_{iss}$	-	280	-	pF	$V_{GS}=0\text{ V}$ , $V_{DS}=100\text{ V}$ , $f=1\text{ MHz}$	
Output capacitance	$C_{oss}$	-	21	-			
Effective output capacitance, energy related <sup>1)</sup>	$C_{o(er)}$	-	14	-			$V_{GS}=0\text{ V}$ , $V_{DS}=0\dots480\text{ V}$
Effective output capacitance, time related <sup>2)</sup>	$C_{o(tr)}$	-	57	-			$I_D=\text{constant}$ , $V_{GS}=0\text{ V}$ $V_{DS}=0\dots480\text{ V}$
Turn-on delay time	$t_{d(on)}$	-	10	-	ns	$V_{DD}=400\text{ V}$ , $V_{GS}=10\text{ V}$ , $I_D=1.9\text{ A}$ , $R_G=12.2\text{ }\Omega$ (see table 20)	
Rise time	$t_r$	-	8	-			
Turn-off delay time	$t_{d(off)}$	-	60	-			
Fall time	$t_f$	-	13	-			

1)  $C_{o(er)}$  is a fixed capacitance that gives the same stored energy as  $C_{oss}$  while  $V_{DS}$  is rising from 0 to 80%  $V_{(BR)DSS}$

2)  $C_{o(tr)}$  is a fixed capacitance that gives the same charging time as  $C_{oss}$  while  $V_{DS}$  is rising from 0 to 80%  $V_{(BR)DSS}$

**Table 8 Gate charge characteristics**

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Gate to source charge	$Q_{gs}$	-	1.5	-	nC	$V_{DD}=480\text{ V}$ , $I_D=1.9\text{ A}$ , $V_{GS}=0\text{ to }10\text{ V}$
Gate to drain charge	$Q_{gd}$	-	6.5	-		
Gate charge total	$Q_g$	-	13	-		
Gate plateau voltage	$V_{plateau}$	-	5.4	-	V	

**Table 9 Reverse diode characteristics**

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Diode forward voltage	$V_{SD}$	-	0.9	-	V	$V_{GS}=0\text{ V}$ , $I_F=1.9\text{ A}$ , $T_j=25\text{ °C}$
Reverse recovery time	$t_{rr}$	-	220	-	ns	$V_R=400\text{ V}$ , $I_F=1.9\text{ A}$ , $di_F/dt=100\text{ A}/\mu\text{s}$ (see table 22)
Reverse recovery charge	$Q_{rr}$	-	1.5	-	$\mu\text{C}$	
Peak reverse recovery current	$I_{rrm}$	-	12	-	A	

5 Electrical characteristics diagrams

Table 10

Power dissipation TO-220, TO-252, TO-263	Power dissipation TO-220 FullPAK
$P_{tot} = f(T_c)$	$P_{tot} = f(T_c)$

Table 11

Max. transient thermal impedance TO-220, TO-252, TO-263	Max. transient thermal impedance TO-220 FullPAK
$Z_{(thJC)} = f(t_p)$ ; parameter: $D = t_p/T$	$Z_{(thJC)} = f(t_p)$ ; parameter: $D = t_p/T$



Electrical characteristics diagrams

Table 12

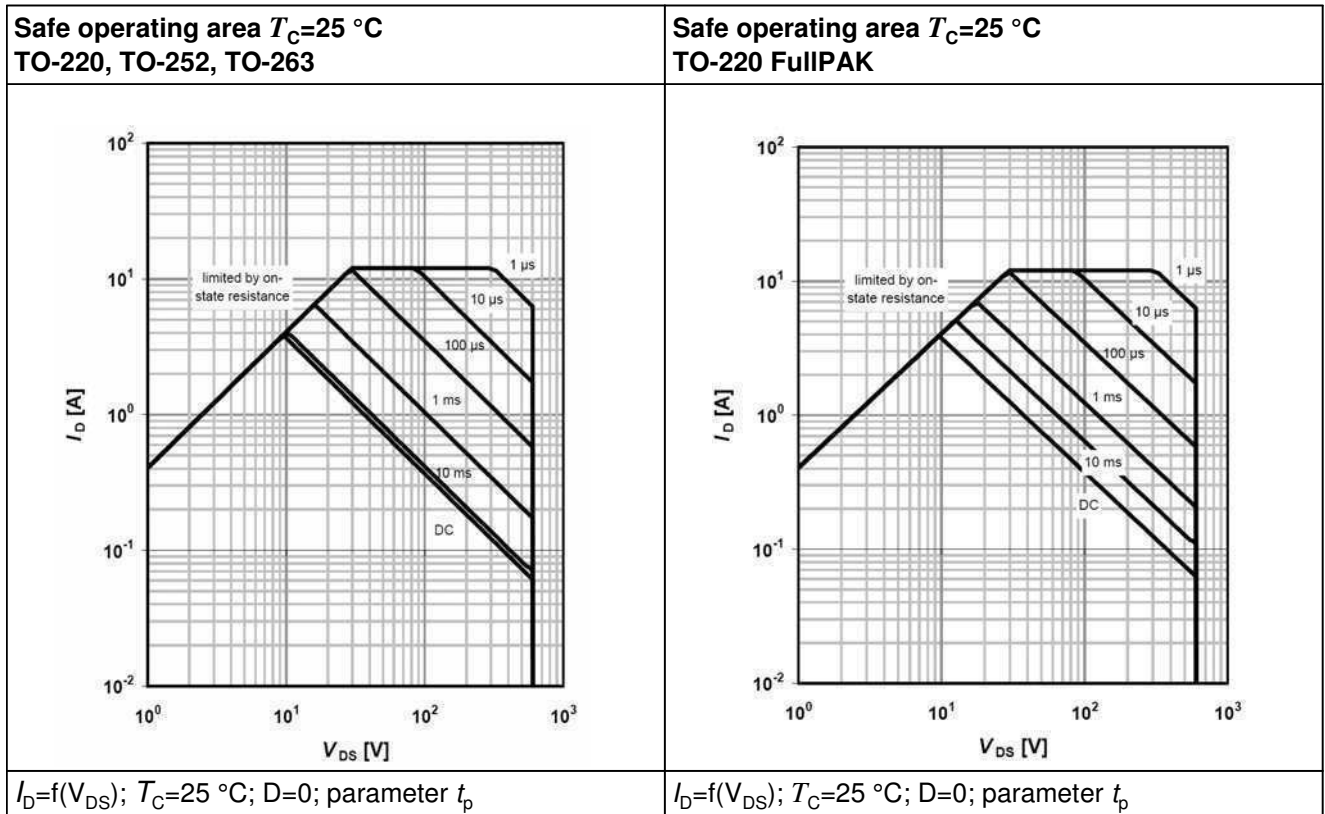


Table 13

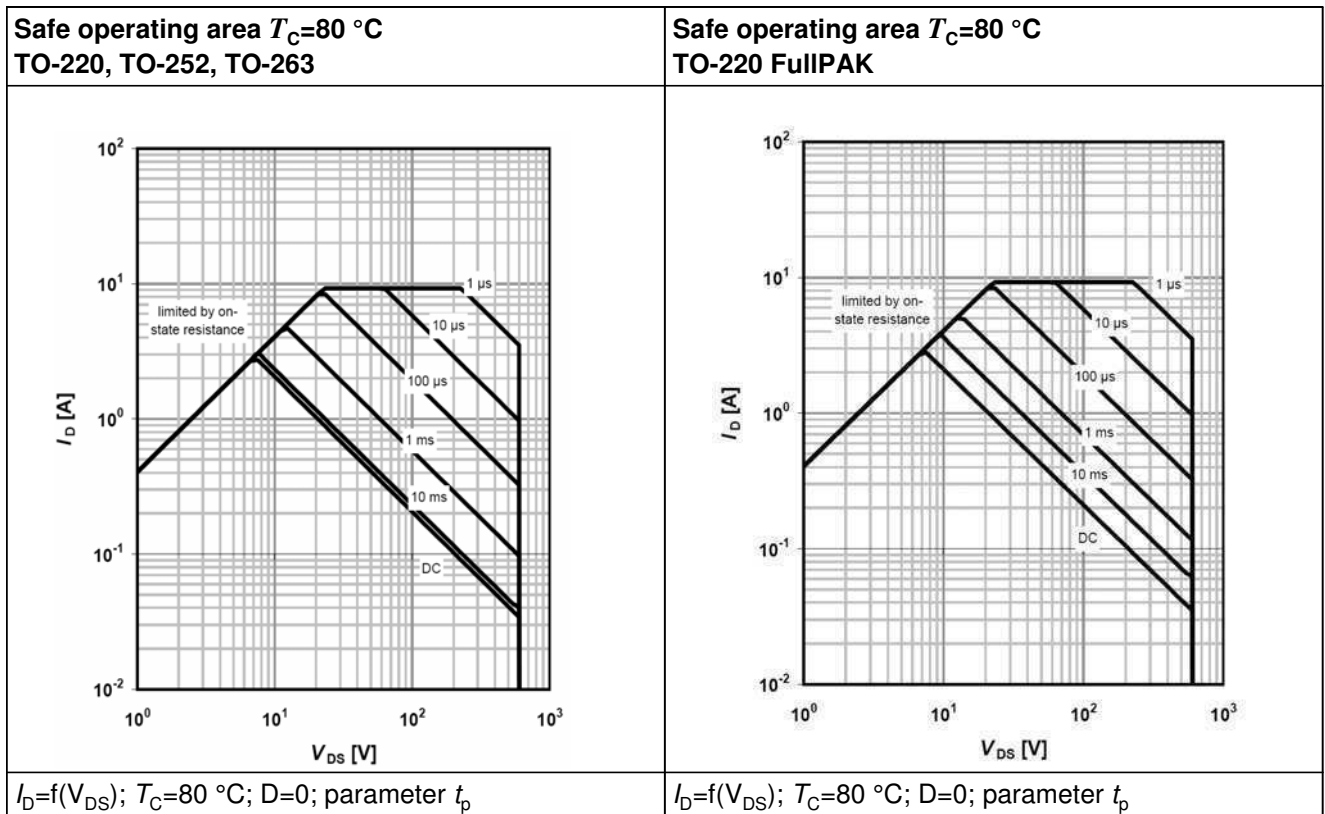


Table 14

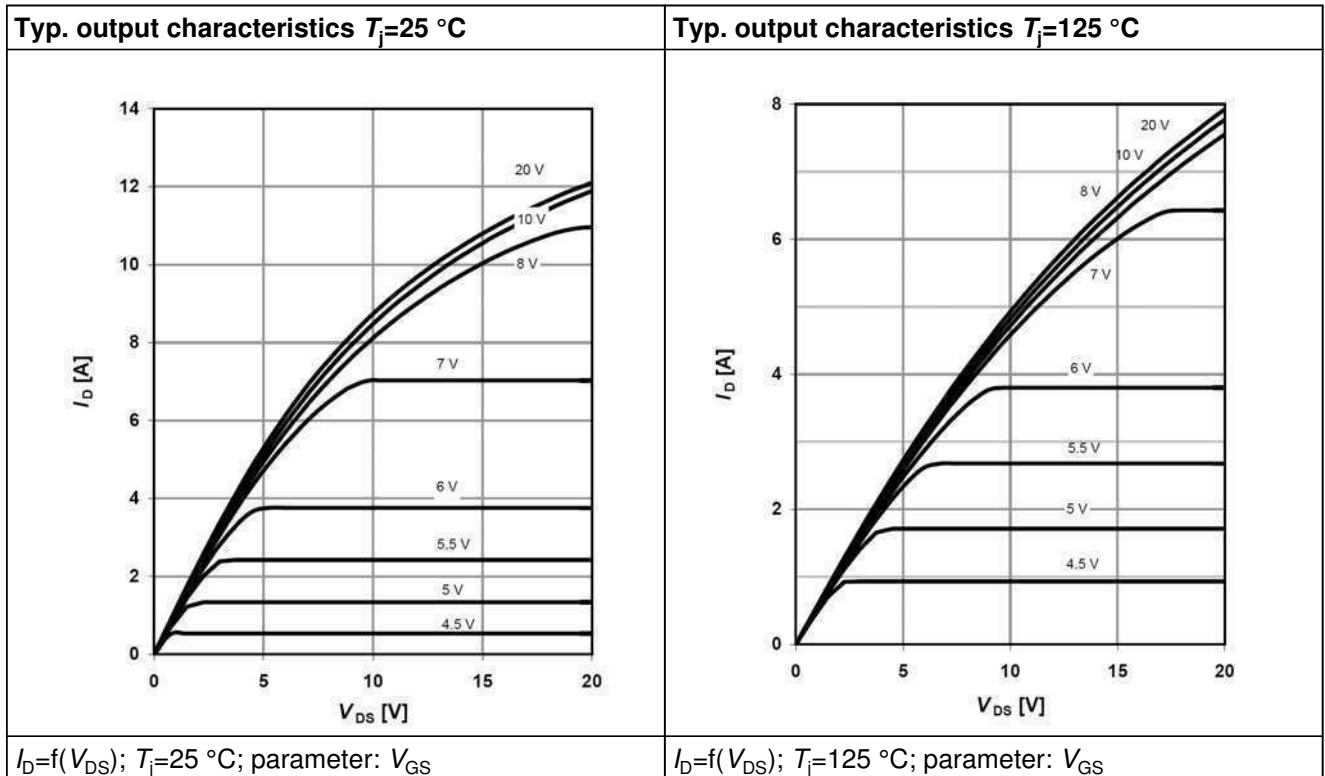


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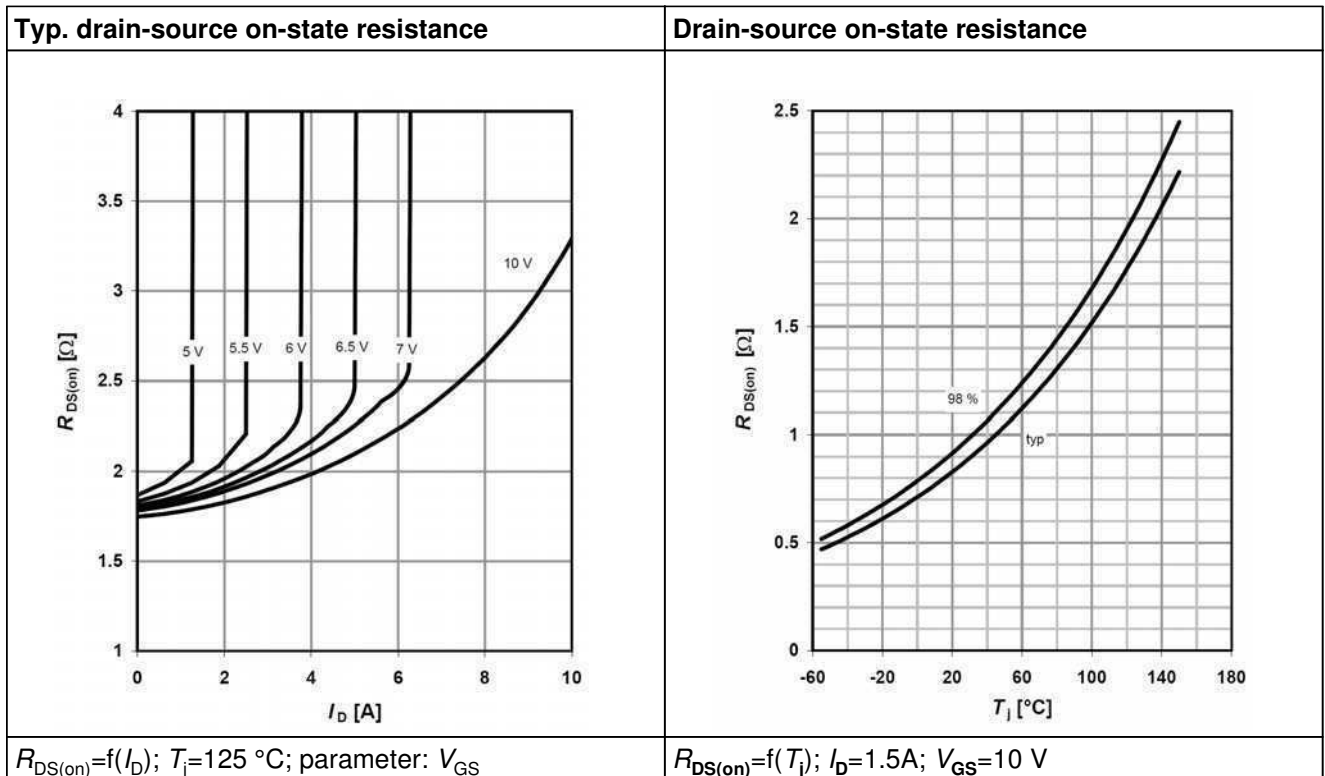


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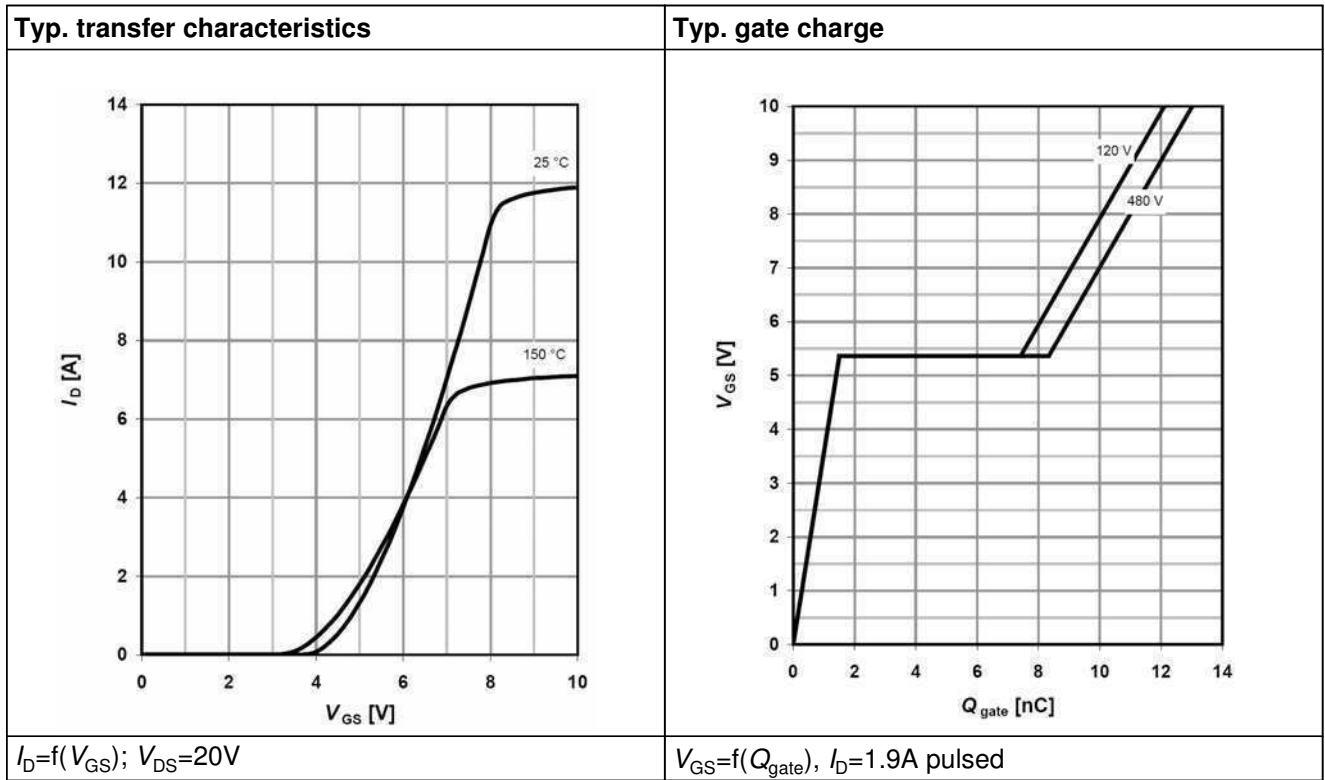


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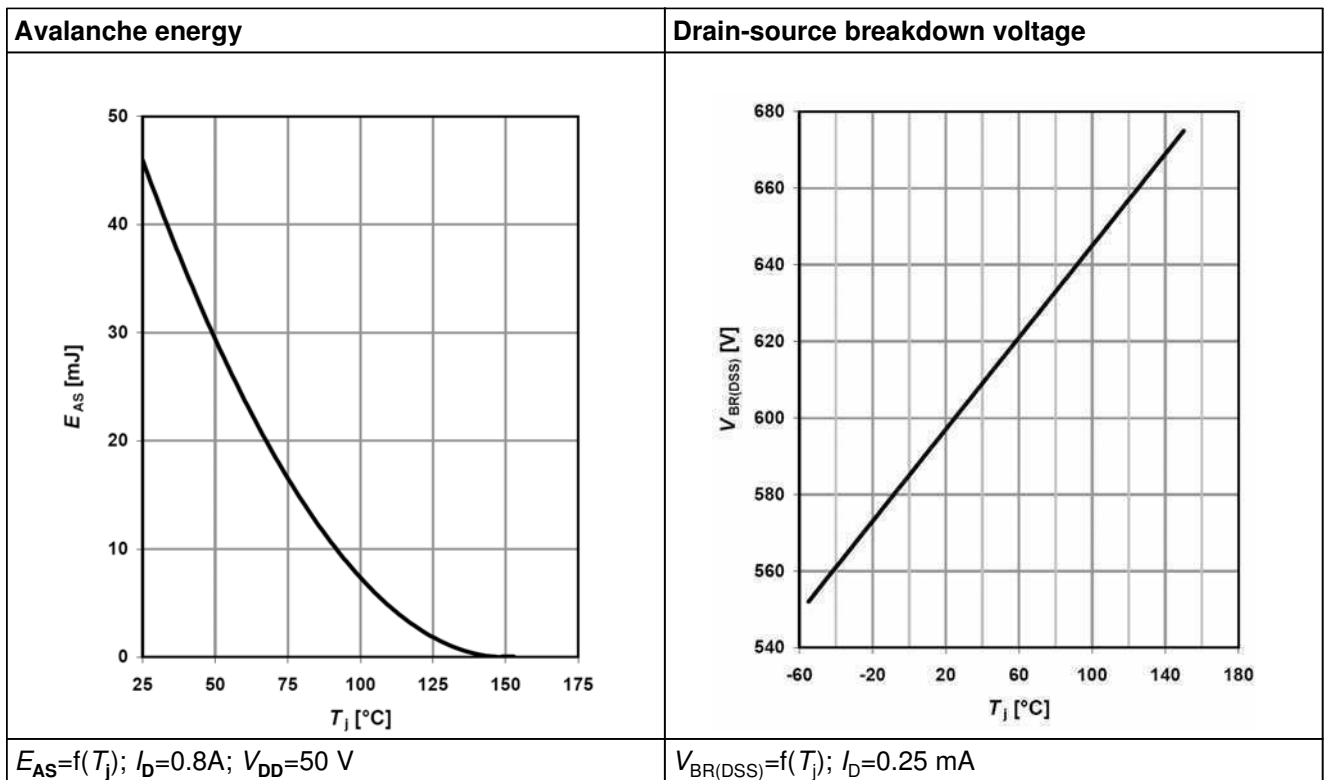


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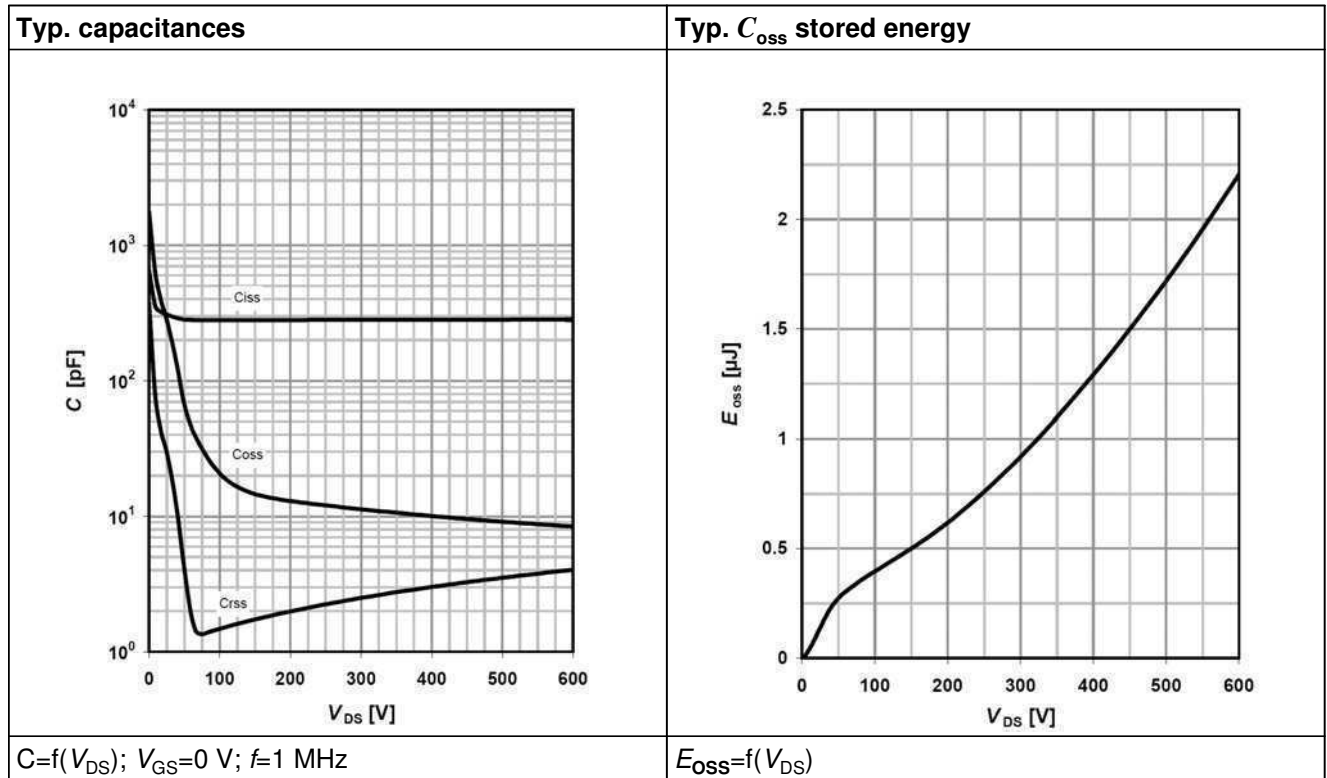
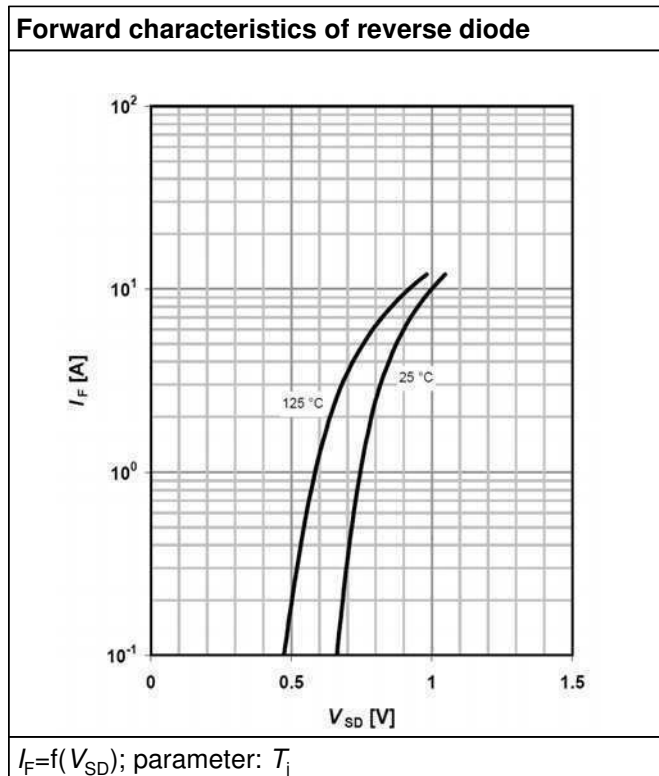


Table 19



## 6 Test circuits

Table 20 Switching times test circuit and waveform for inductive load

Switching times test circuit for inductive load	Switching time waveform

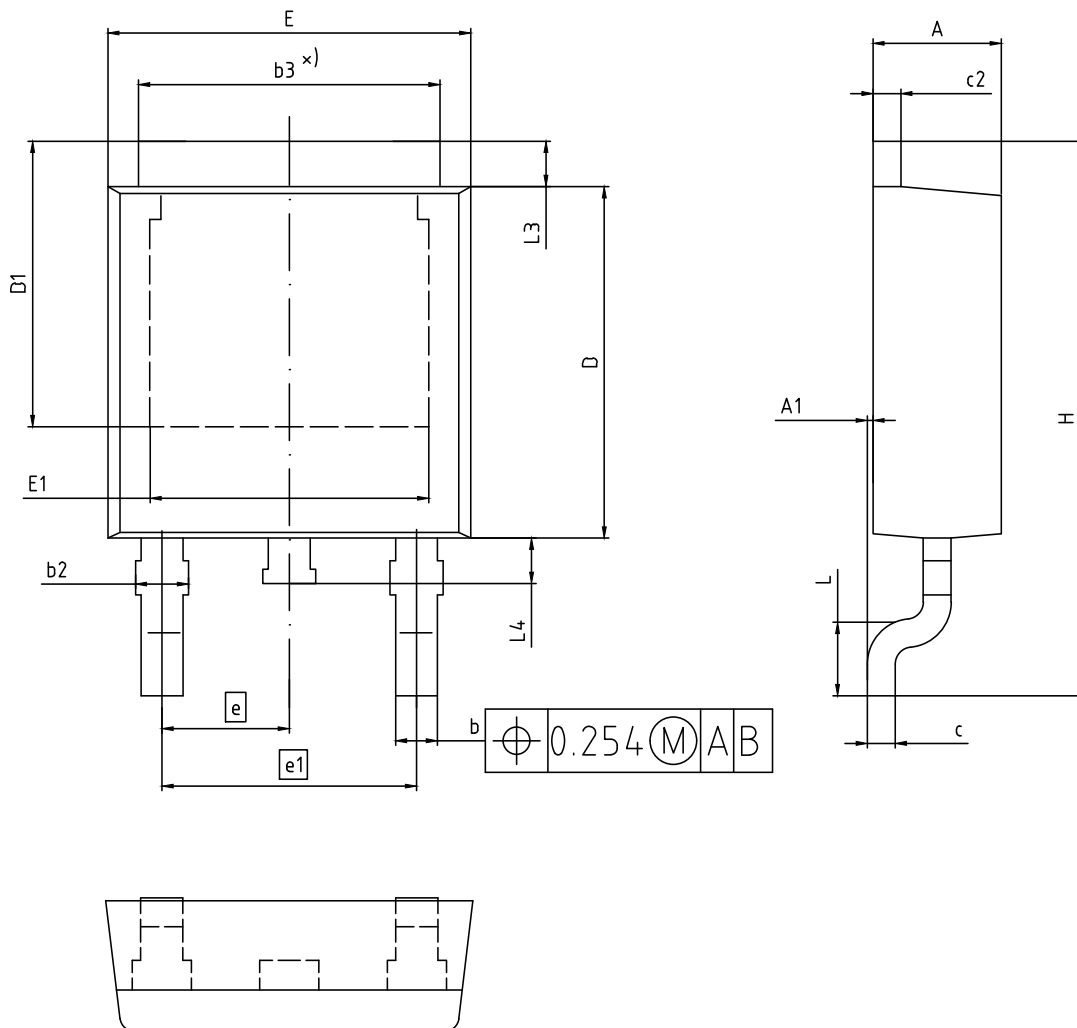
Table 21 Unclamped inductive load test circuit and waveform

Unclamped inductive load test circuit	Unclamped inductive waveform

Table 22 Test circuit and waveform for diode characteristics

Test circuit for diode characteristics	Diode recovery waveform

7 Package outlines

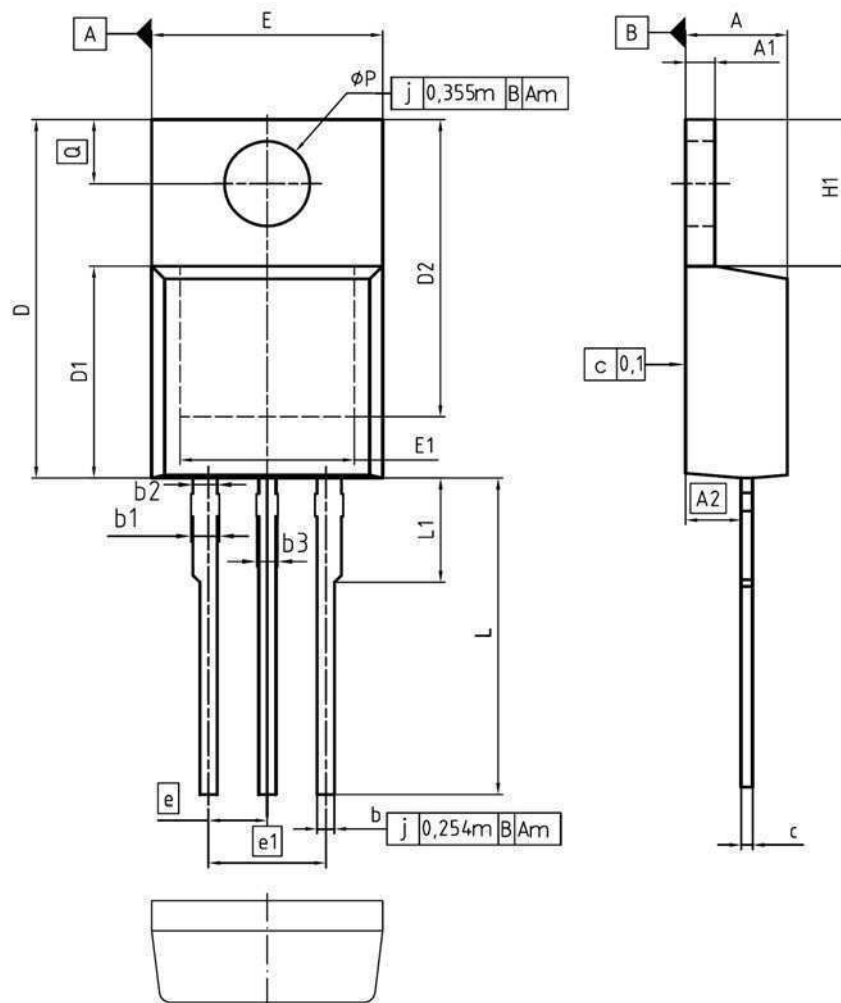


ALL DIMENSIONS REFER TO JEDEC  
STANDARD TO-252 AND DO NOT INCLUDE MOLD  
FLASH OR PROTRUSIONS.

DIMENSION	MILLIMETERS	
	MIN.	MAX.
A	2.16	2.41
A1	0.00	0.15
b	0.64	0.89
b2	0.65	1.15
b3	4.95	5.50
c	0.46	0.61
c2	0.40	0.98
D	5.97	6.22
D1	5.02	5.84
E	6.35	6.73
E1	4.32	5.50
e	2.29	
e1	4.57	
N	3	
H	9.40	10.48
L	1.18	1.78
L3	0.89	1.27
L4	0.51	1.02

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<b>ISSUE DATE</b> 01.04.2020

Figure 1 Outlines TO-252, dimensions in mm



DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	4.30	4.57	0.169	0.180
A1	1.17	1.40	0.046	0.055
A2	2.15	2.72	0.085	0.107
b	0.65	0.86	0.026	0.034
b1	0.95	1.40	0.037	0.055
b2	0.95	1.15	0.037	0.045
b3	0.65	1.15	0.026	0.045
c	0.33	0.60	0.013	0.024
D	14.81	15.95	0.583	0.628
D1	8.51	9.45	0.335	0.372
D2	12.19	13.10	0.480	0.516
E	9.70	10.36	0.382	0.408
E1	6.50	8.60	0.256	0.339
e	2.54		0.100	
e1	5.08		0.200	
N	3		3	
H1	5.90	6.90	0.232	0.272
L	13.00	14.00	0.512	0.551
L1	-	4.80	-	0.189
øP	3.60	3.89	0.142	0.153
Q	2.60	3.00	0.102	0.118

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Figure 2 Outlines TO-220, dimensions in mm/inches

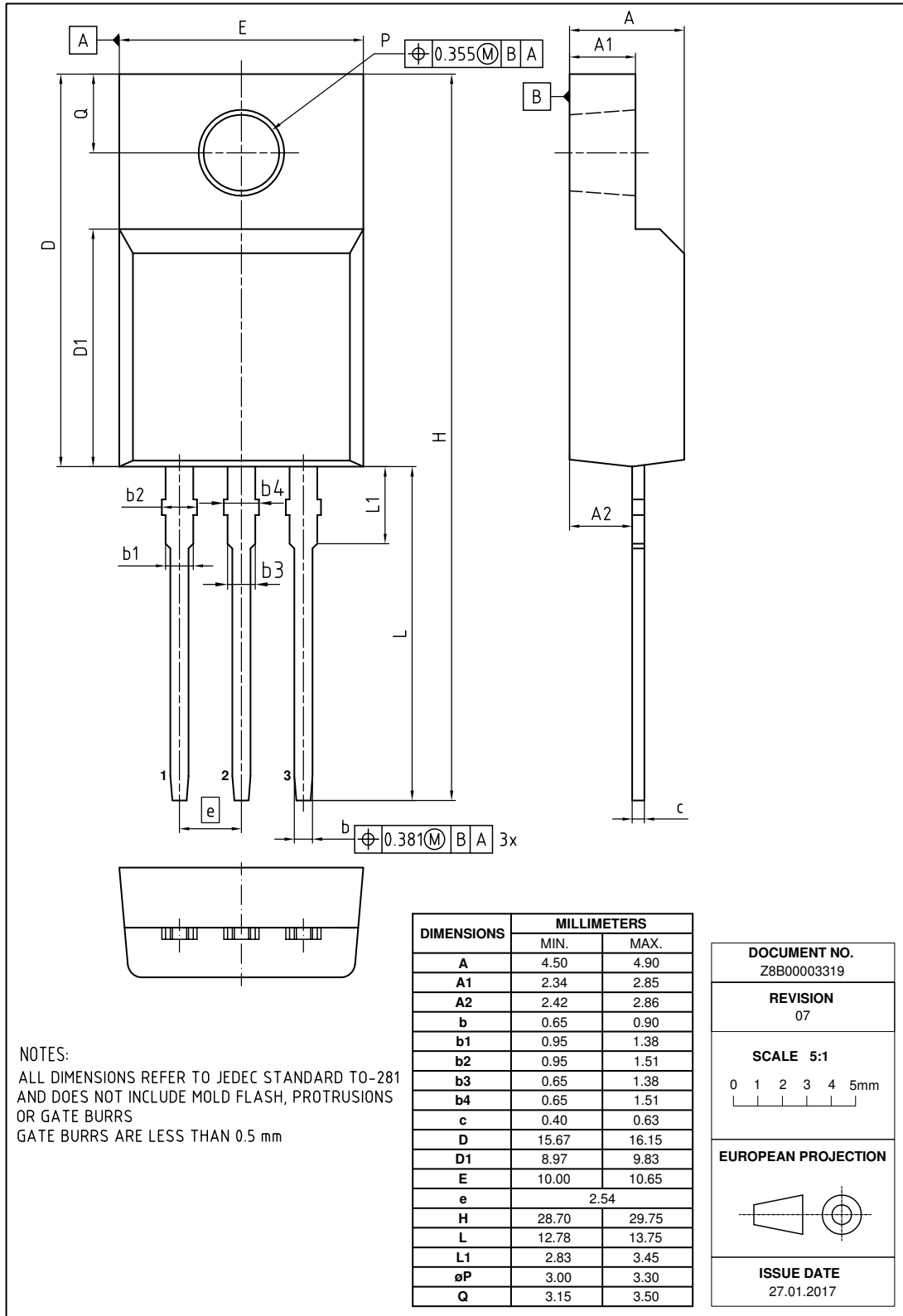


Figure 3 Outlines PG-TO-220 FullPAK, dimensions in mm



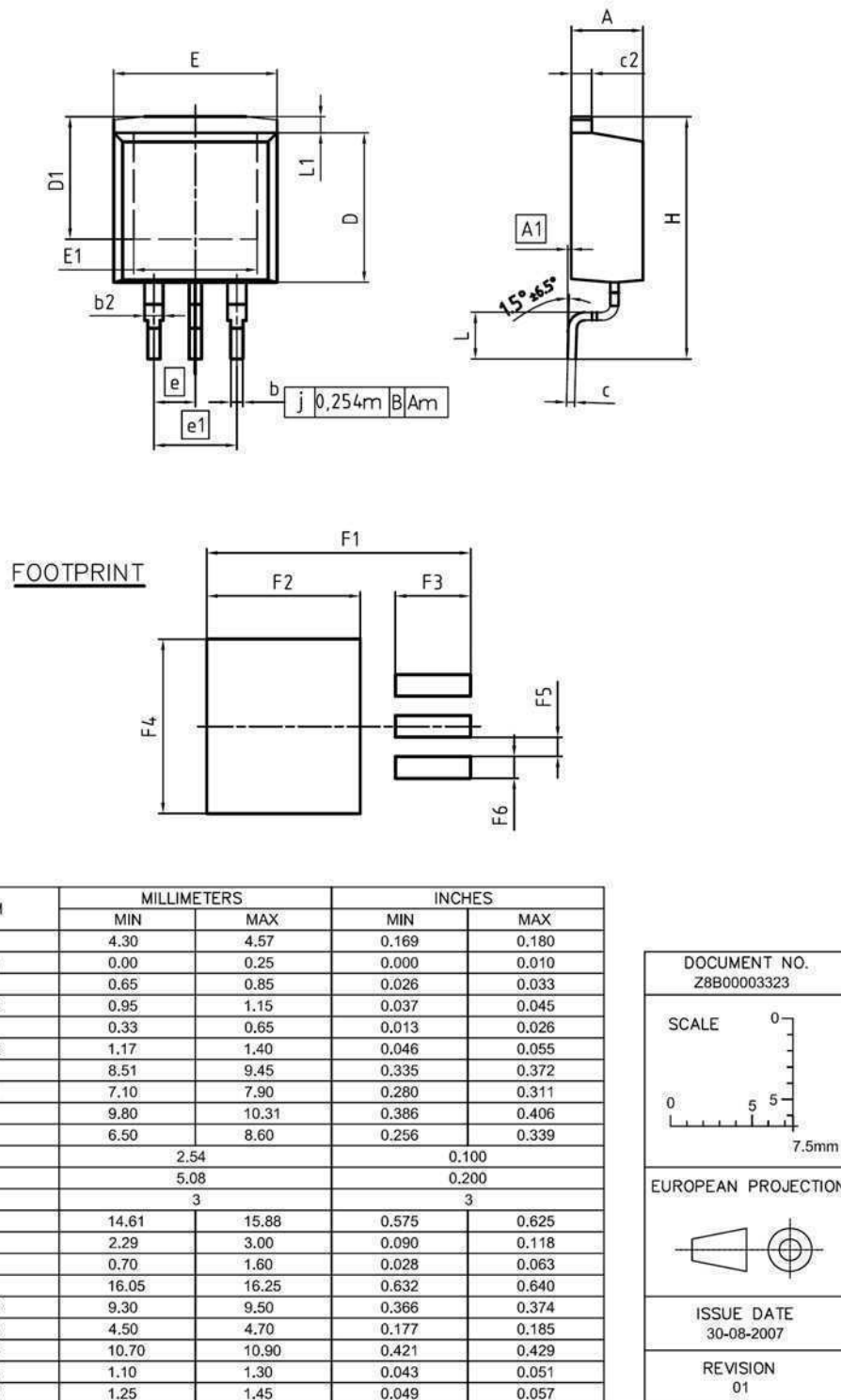


Figure 4 Outlines TO-263, dimensions in mm/inches

## Revision History

IPx60R950C6

**Revision: 2020-05-20, Rev. 2.5**

Previous Revision

Revision	Date	Subjects (major changes since last revision)
2.0	2011-06-08	Release of final Data sheet
2.1	2011-09-14	-
2.2	2015-02-11	PG-TO220 FullPAK package outline update (creation:2014-12-10)
2.3	2015-11-19	Updated with Halogen free logo
2.4	2018-03-06	Outline PG-TO220 FullPAK update
2.5	2020-05-20	Update of the package outlines TO-252

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